

Saurav Roy

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	High-k Oxide Field-Plated Vertical (001) $\text{In}_2\text{Ga}_2\text{O}_3$ Schottky Barrier Diode With Baliga's Figure of Merit Over 1 GW/cm^2 . IEEE Electron Device Letters, 2021, 42, 1140-1143.	2.2	86
2	Low temperature homoepitaxy of (010) $\text{In}_2\text{-Ga}_2\text{O}_3$ by metalorganic vapor phase epitaxy: Expanding the growth window. Applied Physics Letters, 2020, 117, .	1.5	56
3	Multi-kV Class $\text{In}_2\text{-Ga}_2\text{O}_3$ MESFETs With a Lateral Figure of Merit Up to 355 MW/cm^2 . IEEE Electron Device Letters, 2021, 42, 1272-1275.	2.2	50
4	Growth and characterization of metalorganic vapor-phase epitaxy-grown $\text{In}_2\text{-(Al)}$ Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 627 channels. Applied Physics Express, 2021, 14, 025501.	1.1	40
5	130 nm $\text{In}_2\text{-Ga}_2\text{O}_3$ metal semiconductor field effect transistor with low-temperature metalorganic vapor phase epitaxy-regrown ohmic contacts. Applied Physics Express, 2021, 14, 076502.	1.1	39
6	Schottky Barrier Height Engineering in $\text{In}_2\text{-Ga}_2\text{O}_3$ Using SiO_2 Interlayer Dielectric. IEEE Journal of the Electron Devices Society, 2020, 8, 286-294.	1.2	32
7	Design of a $\text{In}_2\text{-Ga}_2\text{O}_3$ Schottky Barrier Diode With p-Type III-Nitride Guard Ring for Enhanced Breakdown. IEEE Transactions on Electron Devices, 2020, 67, 4842-4848.	1.6	21
8	Delta-doped $\text{In}_2\text{-Ga}_2\text{O}_3$ films with narrow FWHM grown by metalorganic vapor-phase epitaxy. Applied Physics Letters, 2020, 117, .	1.5	17
9	In Situ Dielectric $\text{Al}_2\text{O}_3/\text{In}_2\text{-Ga}_2\text{O}_3$ Interfaces Grown Using Metal-Organic Chemical Vapor Deposition. Advanced Electronic Materials, 2021, 7, 2100333.	2.6	17